



# Characterization of Solar Grade Silicon Contaminants

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- All solar technologies can be improved with contamination control.
- Each solar technology has different contaminants that are important.
- Some elements have known effects on PV performance.
- Other elements little known effect.
- Some cell designs are more sensitive than others to the same elements.

- Standards are just emerging that specify contaminants and what levels are acceptable
- Without industry standards materials for PV applications have been described in terms of 'nines' or 'N's (example: 99.99999% pure or 7 nines)
- Number of 'N's does not discriminate between elements that are important and those that are not.
- Number of 'N's excludes elements the measuring technique cannot measure!!
  - For example: Number of 'N's typically excludes atmospheric elements.

# Playing Games with 'Nines'

SIMS Bulk Analysis results				Detection limits
Elements	Conc.(at/cm3)	Conc.(ppba)	Conc.(ppbwt)	Conc.(at/cm3)
<b>B</b>	<b>4.9E+13</b>	<b>0.98</b>	<b>0.38</b>	<b>5E+12</b>
Na	<4.0E+11	<0.008	<0.006	4E+11
Al	<6.0E+12	<0.12	<0.1	6E+12
<b>P</b>	<b>7.2E+13</b>	<b>1.44</b>	<b>1.59</b>	<b>5E+12</b>
Cr	<3.0E+11	<0.006	<0.01	3E+11
Fe	<1.0E+13	<0.20	<0.4	1E+13
Ni	<1.0E+14	<2.00	<4	1E+14
Cu	<1.0E+14	<2.00	<4	1E+14
Zn	<2.0E+14	<4.00	<9	2E+14
K	<4.0E+11	<0.01	<0.01	4E+11
<b>C</b>	<b>&lt;3.0E+15</b>	<b>&lt;60</b>	<b>&lt;25</b>	<b>3E+15</b>
<b>As</b>	<b>8.4E+13</b>	<b>1.68</b>	<b>4.54</b>	<b>5E+12</b>
<b>Sb</b>	<b>7.8E+13</b>	<b>1.56</b>	<b>6.76</b>	<b>1E+13</b>

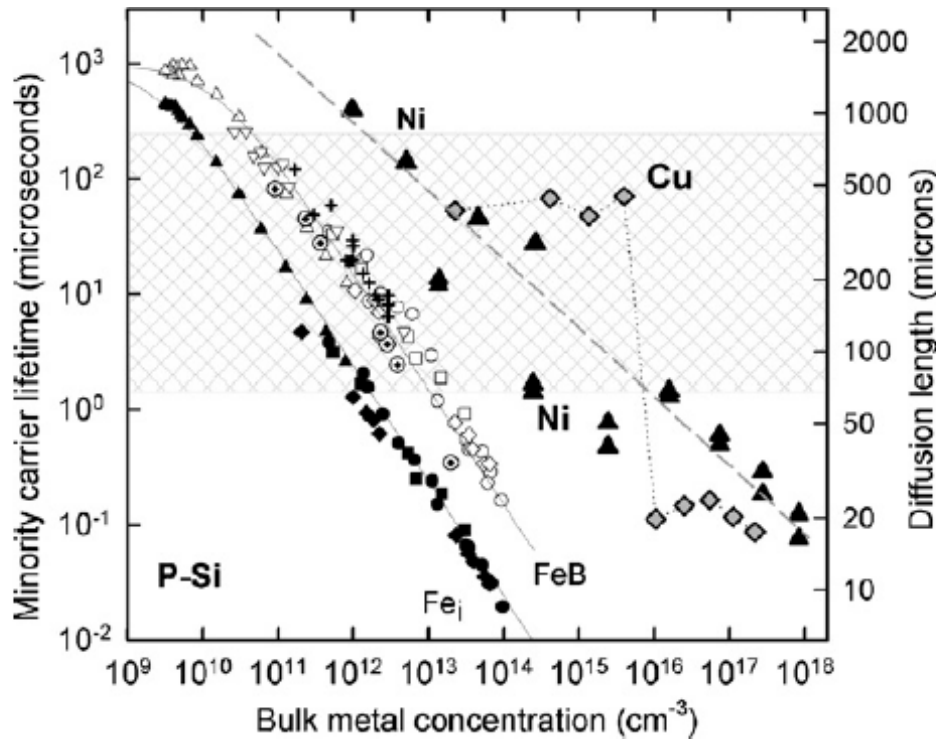
- This silicon has 7N purity considering all listed elements

clude Carbon

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- This silicon has 8N purity of we exclude Carbon

- Materials specifications based on only 'N's make it necessary to reduce all contaminants including those that are not important for PV performance.
- Materials based on 'N's may not emphasize the important elements enough.
- Materials based on 'N's may be more expensive than they need to be.
- For solar PV the contaminants that are most important for performance should be emphasized.



- This work investigated Fe, Ni and Cu.
- Fe had the most effect on lifetime while Cu had less effect.
- This work suggests specifications for solar silicon should emphasize Fe more than Cu.

Fig. 2. Impact of iron, copper, and nickel on minority carrier diffusion length in single-crystalline silicon. The shaded area represents a typical range of minority carrier diffusion lengths in multicrystalline silicon solar cells.

## Control of metal impurities in “dirty” multicrystalline silicon for solar cells

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The Semi organization has developed specifications for solar grade silicon.

There are 4 grades of 'Solar Grade Silicon' with Specifications for:

1. Acceptors: B, Al
  2. Donors: P, As, Sb
  3. Transition and Post Transition Metals: Ti, Cr, Fe, Ni, Cu, Zn, Mo
  4. Alkali and Earth Alkali Metals: Na, K, Ca
  5. Atmospherics: H, C, O, Cl
- The specifications do not mention 'nines' anywhere.
  - Specifications are related to the performance of PV cells.



Grade	I	II	III	IV
Acceptors B,Al	< 1 ppba	< 20 ppba	< 300 ppba	< 1000 ppba
Donors P,As,Sb	< 1 ppba	< 20 ppba	< 50 ppba	< 720 ppba
Bulk O	Not specified	Not specified	Not specified	Not specified
C	< 0.3 ppma	< 2 ppma	< 5 ppma	< 100 ppma
Transition Metals Ti,Cr,Fe,Ni,Cu,Zn,Mo	< 10 ppba	< 50 ppba	< 100 ppba	< 200 ppba
Alkali and Earth Alkali Na,K,Ca	< 10 ppba	< 50 ppba	< 100 ppba	< 4000 ppba
Total H	Low enough so that particles do not explode on heating			
Total Cl	Low enough so that particles do not explode on heating			

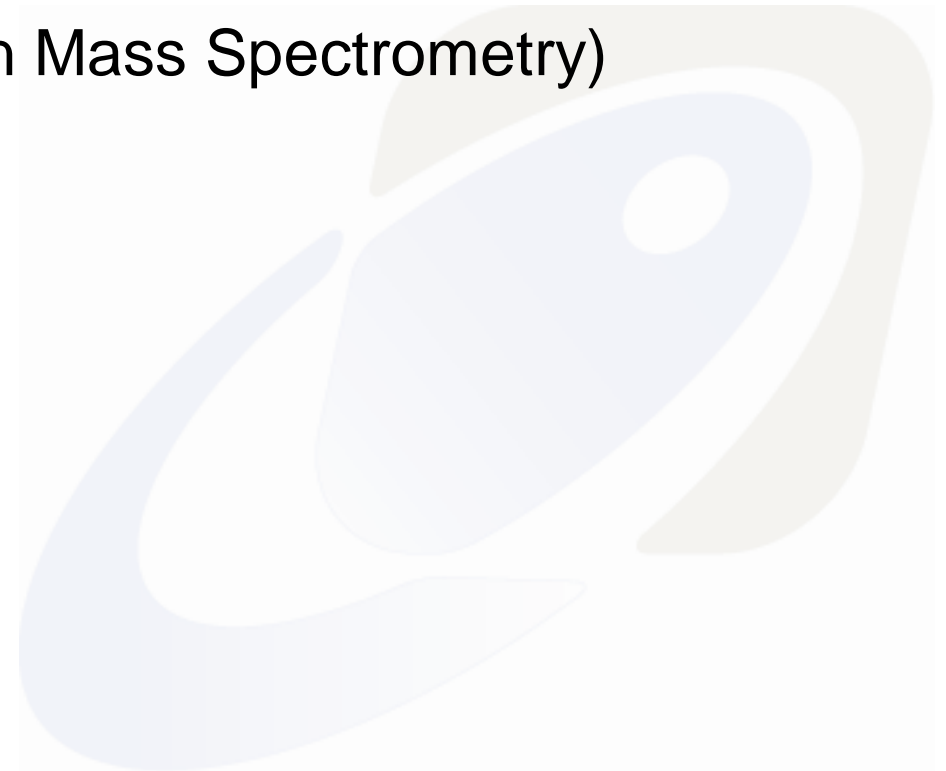


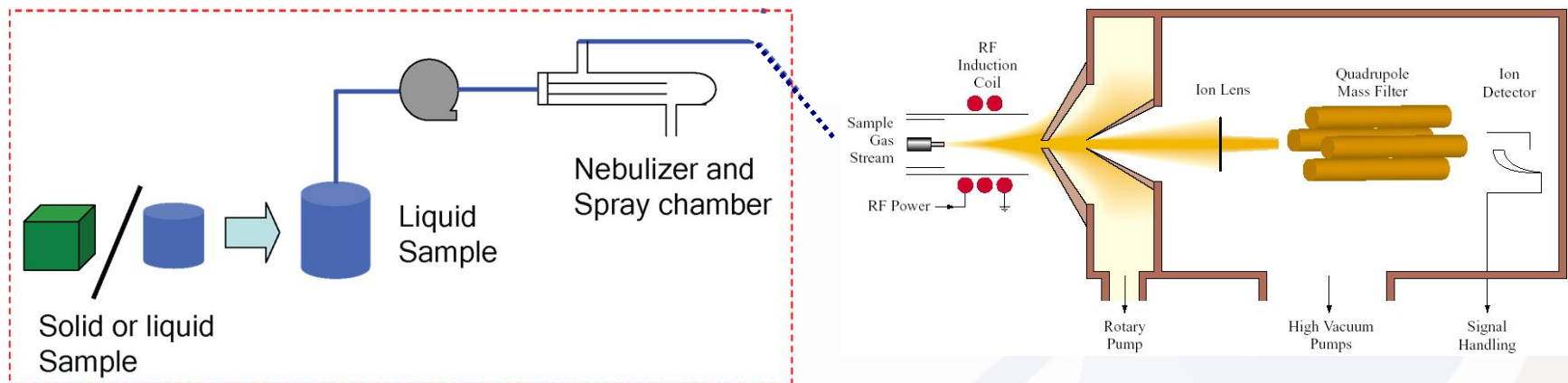
# Measuring Contamination

Analytical Techniques

- There are many methods for measuring contamination in silicon.
- Each has advantages and limitations.
- Detection limits need to be sufficient to report intended level of purity.
- Accuracy is important for comparison to specifications.
- Reproducible measurements are needed for comparison to previous analysis.
- Elements that have high background or cannot be measured need to be specified.

- In this presentation we look at:
  - ICP-MS (Inductively Coupled Plasma Mass Spectrometry)
  - SIMS (Secondary Ion Mass Spectrometry)



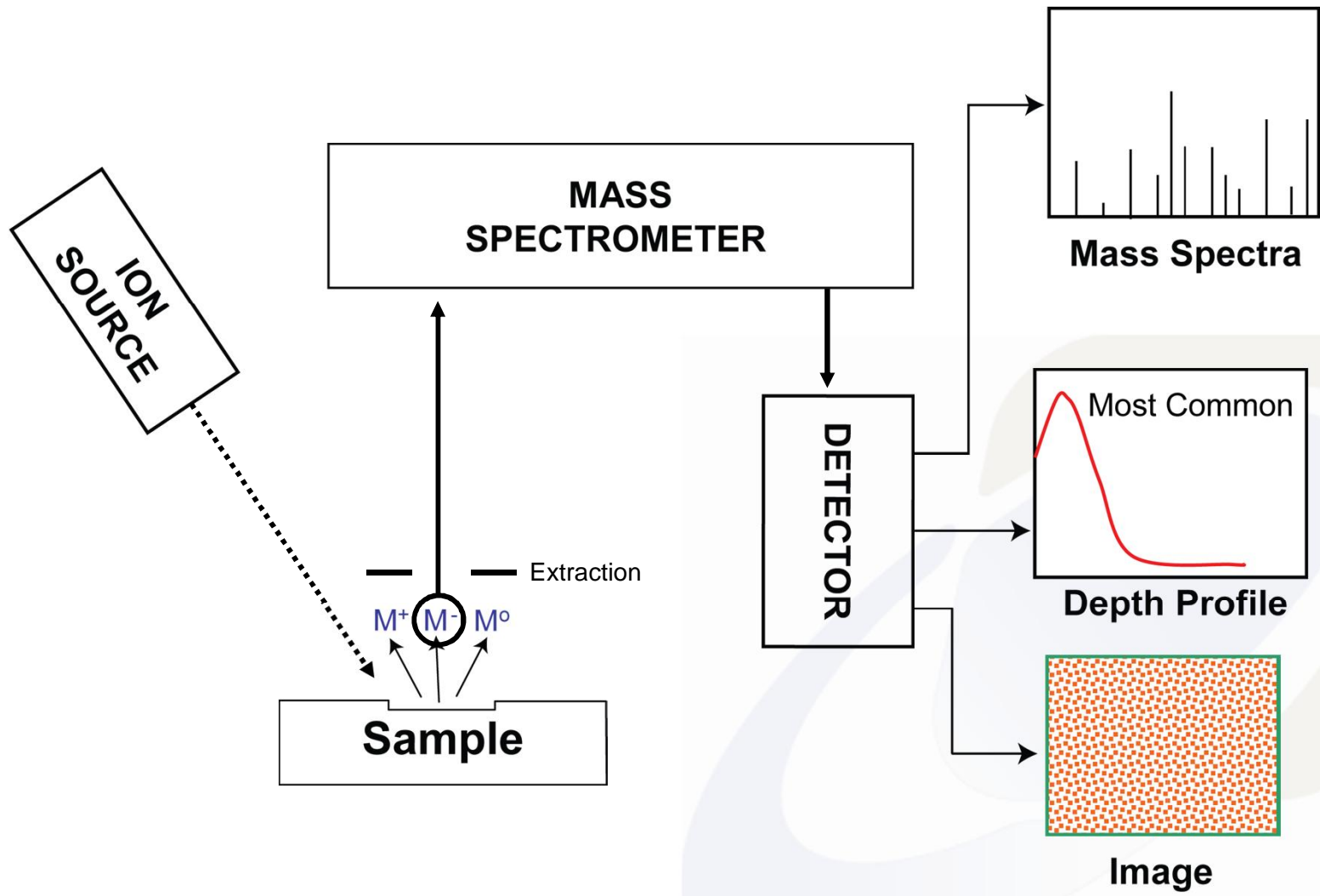


- Survey analysis technique.
- ppm to ppb detection limits depending on element.
- Relatively large sample size.
- Measures whole sample both inside and outside.
- Does not measure 'atmospheric' elements.
- P, an important dopant, can be difficult.
- Sample must be dissolved prior to analysis.
- Sample prep vulnerable to added contamination.
- Dedicated system required for best detection limit.

- Is ICP-MS Accurate?
  - Liquid references are available from NIST. When contaminant concentrations are above 100ppm, then accuracy is +/- 5%. Lower concentrations +/- 30%.
- Is ICP-MS Reproducible?
  - This depends if the samples can be prepared in the same way each time. Precision is about +/- 5%.
- Is sampling Representative?
  - The sample size can be relatively large. Inhomogeneity in the sample will be evened out.
  - The sample must be dissolved prior to analysis. This needs to be done without losing material and without adding material.
  - With proper technique and procedures, the sample can be representative of the original material.

- Does the sampling method change the sample?
  - Yes and in a very fundamental way. We are converting a solid into a liquid.
- Understand WHAT is being measured.
  - By dissolving the sample we are including contamination from the outside of the sample.
  - It may be important to include surface contamination in which case sample handling is important.
  - It may be important NOT to include surface contamination in which case sample cleaning or another analysis may be more suitable.





- ppm to ppt detection limits depending on element.
- DOES measure 'atmospheric' elements H,C,N,O.
- Sample does NOT need to be dissolved.
- Sample prep contamination is not an issue.
- Direct sampling of all forms of PV materials.
- Measures the sample inside.
- Smaller sample size than ICP-MS
- **A few elements at one time for best detection limit.**

- Is SIMS Accurate?
  - Accuracy depends on the quality of the standard. With NIST standards for B, P and As in Si, accuracy is +/- 3%. With ion implant standards, +/- 15%. Without standards SIMS is not accurate.
- Is SIMS Reproducible?
  - Precision is +/- 5% to 10% depending on element.
- Is sampling Representative?
  - SIMS bulk measurement samples the interior and excludes the surface. Thus it is representative of the sample bulk.
  - Analysis area is a few hundred microns. Measurement will not be representative if inhomogeneity occurs over a larger scale.
  - SIMS profiling can show changes from outside to inside.

- Does the sampling method change the sample?
  - SIMS is a direct sampling technique so the sample is not altered prior to analysis. Particle and granule type material are mounted and cross-sectioned prior to analysis.
- Understand WHAT is being measured.
  - SIMS bulk measurement is true bulk, excluding and surface contamination contributions.
  - SIMS profiling can be done from the outside in to see difference in exterior vs. interior contamination.



# Case Study: Contamination in Powders

ICP-MS and SIMS



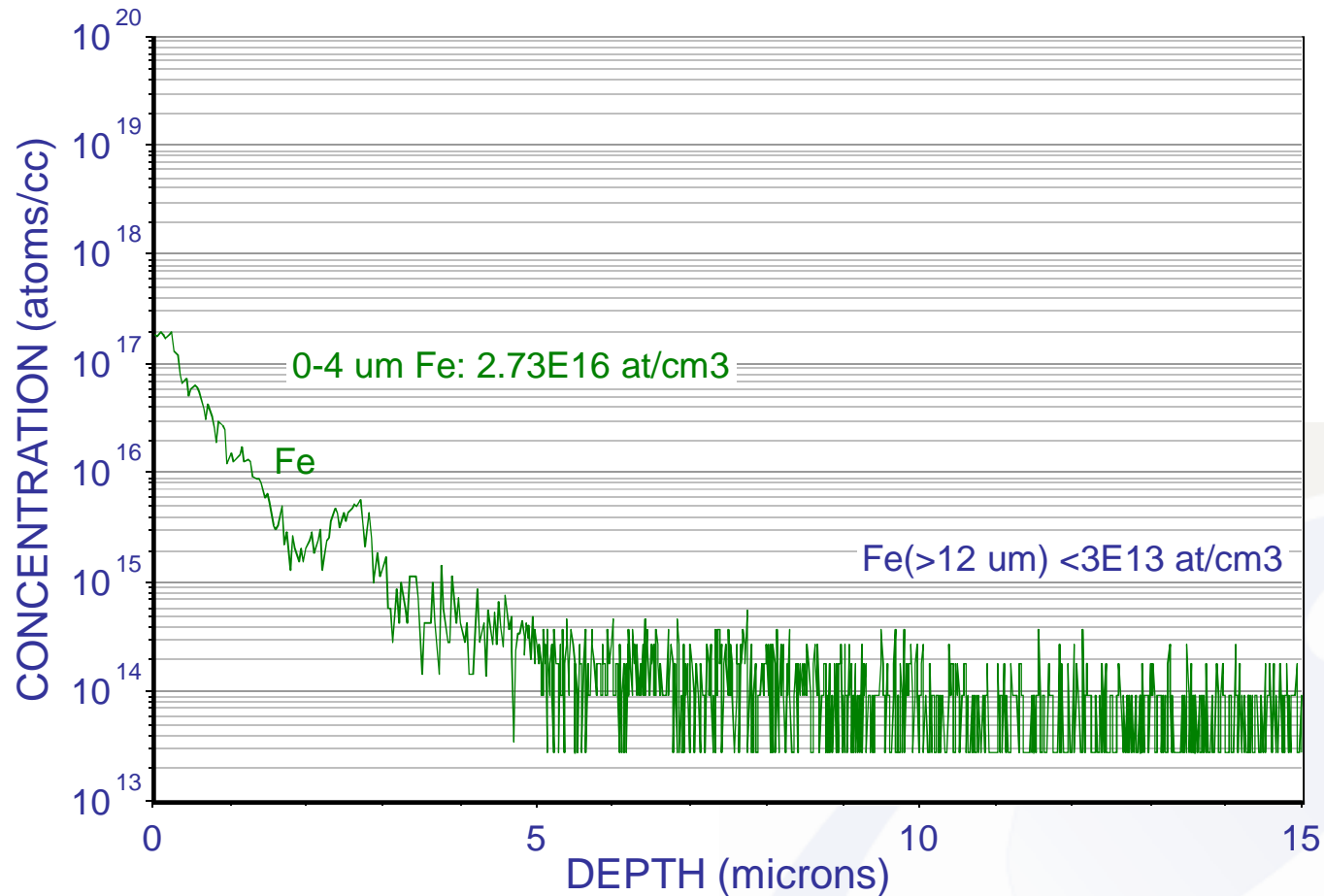
	SIMS	ICP-MS
B	1.1	0.8
C	9	-
O	30	-
Al	0.3	0.4
P	8.1	11.4
Cr	<7E-5	<0.01
Fe	<0.001	1.3
Ni	<0.008	<0.01
As	0.07	-

Methods often show different results. Why?



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Al	0.3	0.4
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<b>Fe</b>	<b>&lt;0.001</b>	<b>1.3</b>
Ni	<0.008	<0.01
As	0.07	-

- Test results from different methods often show different results.
- Fe shows great differences, why?



- GDMS measures both inside and outside the particles and some Fe surface contamination will be included.
- SIMS bulk measurement excludes the surface contamination.



- ‘Number of Nines’ can be a misleading measure of purity.
- Progress has been made defining what is meant by ‘Solar Grade Silicon’ with values relevant to PV performance.
- Contamination measurement techniques can show different numbers from the same material. We must understand what is being measured.